AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph starting at page 4, line 17 as follows:

Herein, the GaN-based buffer layer 102 can be formed having a triple-structured ~~$Al_yIn_xGa_{1-x-y}N/In_xGa_{1-x}N/GaN$ (Here, $0 \leq x \leq 1$, $0 \leq y \leq 1$)~~ $Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN$ (where $0 \leq x \leq 1$, $0 \leq y \leq 1$) laminated, a double-structured $In_xGa_{1-x}N/GaN$ (~~Here,~~ where $0 \leq x \leq 1$) laminated, or a super-lattice-structured (SLS) $In_xGa_{1-x}N/GaN$ (~~Here,~~ where $0 \leq x \leq 1$) laminated.

Please amend the paragraph starting at page 5, line 8 as follows:

Additionally, in a process of growing-up the GaN-based buffer layer 102 on the substrate 101 at a low temperature, a metal organic chemical vapor deposition (MOCVD) equipment is used such that it is, in a growth pressure of 100-700torr and at a low temperature of 500-800℃, grown-up to have a thickness of below 700 Å in a laminated structure such as the triple-structured ~~$Al_yIn_xGa_{1-x-y}N/In_xGa_{1-x}N/GaN$~~ $Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN$, the double-structured $In_xGa_{1-x}N/GaN$ or the super-lattice-structured (SLS) $In_xGa_{1-x}N/GaN$, etc.

Please amend the paragraph starting at page 6, line 10 as follows:

Referring to FIG. 2, in the inventive nitride semiconductor LED, on the substrate 201 (for example, the sapphire substrate or the SiC substrate) is provided the GaN-based buffer layer 202 having the triple-structured ~~$Al_yIn_xGa_{1-x-y}N/In_xGa_{1-x}N/GaN$ (Here, $0 \leq x \leq 1$, $0 \leq y \leq 1$)~~ $Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN$ (where $0 \leq x \leq 1$, $0 \leq y \leq 1$), the double-structured $In_xGa_{1-x}N/GaN$ (Here, $0 \leq x \leq 1$), or the super-lattice-structured (SLS) $In_xGa_{1-x}N/GaN$ (~~Here,~~ where $0 \leq x \leq 1$). Additionally, on the GaN-based buffer layer 202 is formed the undoped GaN layer or the indium-doped GaN layer 203.

Please amend the paragraph starting at page 9, line 15 as follows:

Here, on the substrate 301 is provided the GaN-based buffer layer 302 having the triple-structured ~~$Al_yIn_xGa_{1-x-y}N/In_xGa_{1-x}N/GaN$ (Here, $0 \leq x \leq 1$, $0 \leq y \leq 1$)~~ $Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN$ (where $0 \leq x \leq 1$, $0 \leq y \leq 1$), the double-structured $In_xGa_{1-x}N/GaN$ (~~Here,~~ where $0 \leq x \leq 1$) or the super-lattice-structured (SLS) $In_xGa_{1-x}N/GaN$ (Here, $0 \leq x \leq 1$). Additionally, on the GaN-based buffer layer 302 is formed an undoped GaN layer or an indium-doped GaN layer 303.